Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claims 1, 6, 7 and 12-18 without prejudice or disclaimer.

Please rewrite claims 2, 3, 5 and 8-11, and add new add new claim 19 as follows:

Listing of Claims:

Claim 1 (cancelled)

2. (currently amended) A fabricating apparatus as defined in claim ~~1~~19, wherein the whole of the reactor ~~is made of~~comprises the aluminum nitride material.

3. (currently amended) A fabricating apparatus as defined in claim ~~1~~19, wherein the reactor is composed of a reactor body ~~made of~~comprising a silicon oxide-based material and an aluminum nitride film is coated on the inner wall of the reactor body.

4. (original) A fabricating apparatus as defined in claim 3, wherein the aluminum nitride film is formed by a thermal CVD method.

5. (currently amended) A fabricating apparatus as defined in claim ~~1~~19, wherein the part of the reactor to be contacted with the aluminum chloride gas ~~is made of~~comprises the aluminum nitride material and the rest of the reactor comprises ~~is made of~~ a silicon oxide-based material.

Claims 6-7 (cancelled)

8. (currently amended) An apparatus for fabricating a III-V nitride film including at least Al ~~element~~ on a given substrate ~~by~~ using a Hydride Vapor Phase Epitaxy method, comprising a double reactor structure ~~reactor~~ constructed of an inner reactor to hold a substrate and at least an aluminum metallic material therein and an outer

reactor surrounding the inner reactor ~~which are made of~~comprising a silicon oxide-based material, a gas-supplying means to introduce chloride-based gas, ammonia gas and carrier gas into the inner reactor, a heater to heat the interior of the inner reactor, and a gas leak-detecting means with a gas concentration sensor to detect ~~the~~ gas ~~leak in~~ leaks between the inner reactor and the outer reactor.

9. (currently amended) A fabricating apparatus as defined in claim 8, ~~wherein~~further comprising means for generating a given pressure difference ~~is generated in~~ between the inner reactor and the outer reactor, and ~~then, the gas concentration sensor is set to detect~~means for detecting a given gas concentration in either the inner reactor or the outer reactor which is lower in pressure, said means for detecting said given gas concentration comprising a gas concentration sensor.

10. (currently amended) A fabricating apparatus as defined in claim 9, wherein said means for generating a given pressure sets the interior pressure of the outer reactor ~~is set~~ to be lower than that of the inner reactor, and ~~then, the~~said gas concentration sensor is set to detect ~~a~~ said given gas concentration in the outer reactor.

11. (currently amended) A fabricating apparatus as defined in any one of claims 8-10, wherein the gas concentration sensor ~~detects~~comprises at least one selected from the group consisting of an ammonia gas sensor, a hydrogen chloride gas sensor and an inert gas sensor.

Claims 12-18 (cancelled)

19. (New) A Hydride Vapor Phase Epitaxy apparatus for fabricating a Group III-V nitride film including at least Al, comprising:

a reactor having an upstream zone and a downstream zone, at least a portion of the reactor that is exposed to an aluminum chloride gas comprising an aluminum nitride material;

gas-supplying means for supplying chloride-based gas and ammonia gas into the reactor;

a material holder for holding at least an aluminum metallic material provided in the upstream zone of the reactor; and

a substrate holder for holding a substrate provided in the downstream zone of the reactor.